Supplemental Information for:

High Performance Organic Field-Effect Transistors using Ambient Deposition of Tetracene Single Crystals

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**Figure S1.** Typical current response for a device in which there was an incomplete removal of the liquid solvent layer. Gate voltages shown were -80 V, -60 V, -40 V, and -20 V.

**Figure S2.** The width-normalized contact resistance of the device shown in Figure 4 as a function of $V_G - V_T$. The contact resistance was estimated using $R_{tot} = R_c + \frac{L}{W\mu C_i(V_G - V_T)}$, as discussed in [38].